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Figure 1A
(Prior Art)

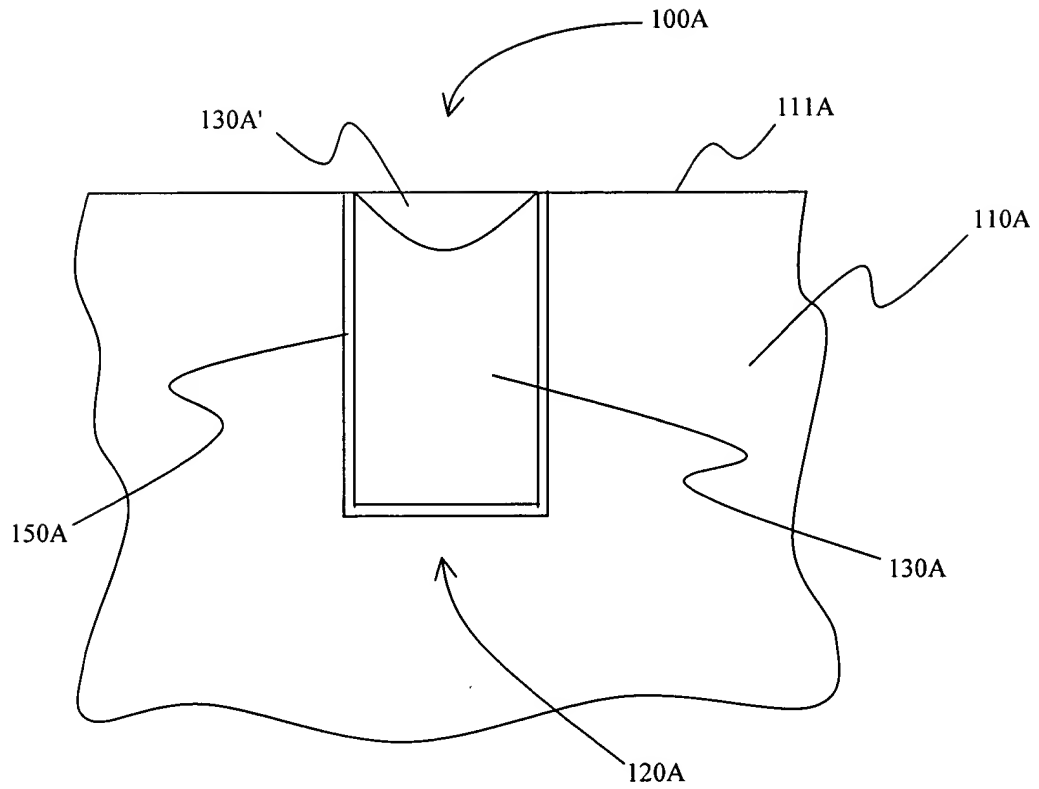
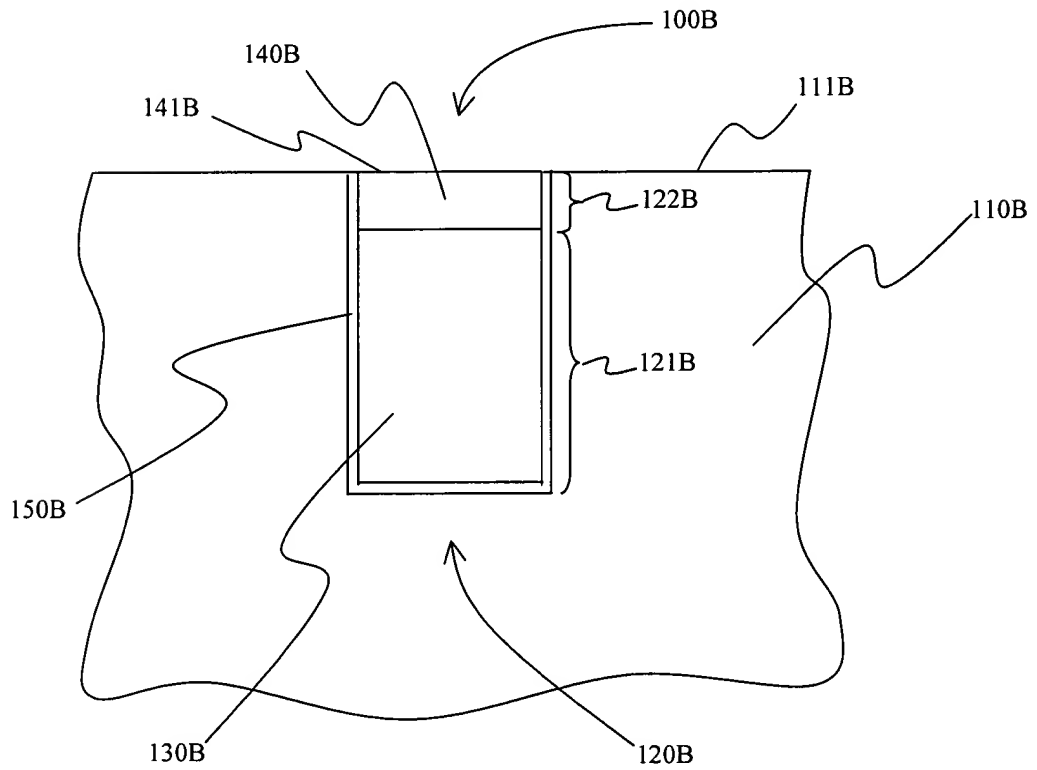


Figure 1B



200



210

Forming a trench in a substrate having a surface, and depositing a first compound into the trench using spin-on deposition

220

Partially removing the first compound from the trench such that an upper surface of the compound is below the surface of the substrate

230

Depositing a second compound onto the surface and onto the upper surface of the first compound by chemical vapor deposition

240

Planarizing the isolation structure such that the surface of the substrate and an upper surface of the second compound are substantially coplanar

Figure 2